

Is Now Part of



# **ON Semiconductor**®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lay bed ON Semiconductor and its officers, employees, ween if such claim alleges that ON Semiconductor was negligent regarding the d



# MOC3051M, MOC3052M 6-Pin DIP Random-Phase Triac Driver Optocoupler (600 Volt Peak)

## **Features**

- Excellent I<sub>FT</sub> Stability—IR Emitting Diode Has Low Degradation
- 600 V Peak Blocking Voltage
- Safety and Regulatory Approvals
  - UL1577, 4,170 VAC<sub>RMS</sub> for 1 Minute
  - DIN EN/IEC60747-5-5

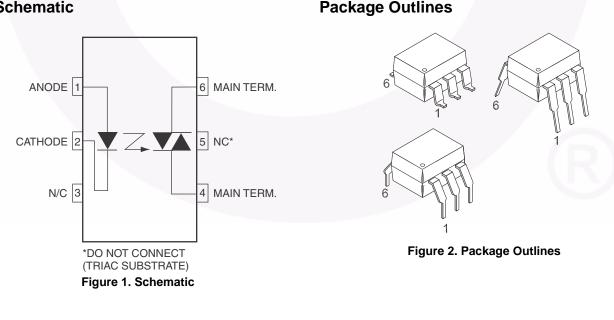
## Applications

- Solenoid/Valve Controls ٠
- Lamp Ballasts
- Static AC Power Switch
- Interfacing Microprocessors to 115  $V_{AC}$  and 240  $V_{AC}$ Peripherals
- Solid State Relay
- Incandescent Lamp Dimmers
- **Temperature Controls**
- Motor Controls

## Description

The MOC3051M and MOC3052M consist of a GaAs infrared emitting diode optically coupled to a non-zerocrossing silicon bilateral AC switch (triac). These devices isolate low voltage logic from 115  $V_{AC}$  and 240  $V_{AC}$  lines to provide random phase control of high current triacs or thyristors. These devices feature greatly enhanced static dv/dt capability to ensure stable switching performance of inductive loads.





## Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		40/85/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
V PR	$V_{PR} = \frac{1}{100\%} $		V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥7	mm
	External Clearance	≥7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V	> 10 <sup>9</sup>	Ω

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Parameters	Value	Unit	
Total Dev	ice			
T <sub>STG</sub>	Storage Temperature	-40 to +150	°C	
T <sub>OPR</sub>	Operating Temperature	-40 to +85	°C	
ТJ	Junction Temperature Range	-40 to +100	°C	
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 seconds	°C	
	Total Device Power Dissipation at 25°C Ambient	330	mW	
PD	Derate Above 25°C	4.4	mW/°C	
Emitter				
١ <sub>F</sub>	Continuous Forward Current	60	mA	
V <sub>R</sub>	Reverse Voltage	3	V	
Б	Total Power Dissipation at 25°C Ambient	100	mW	
PD	Derate Above 25°C	1.33	mW/°C	
Detector				
V <sub>DRM</sub>	Off-State Output Terminal Voltage	600	V	
I <sub>TSM</sub>	Peak Non-Repetitive Surge Current (Single Cycle 60 Hz Sine Wave)	1	А	
р	Total Power Dissipation at 25°C Ambient	300	mW	
PD	Derate Above 25°C	4	mW/°C	

# **Electrical Characteristics**

 $T_A = 25^{\circ}C$  unless otherwise specified.

#### **Individual Component Characteristics**

Symbol	Parameters	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER						
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 10 mA		1.18	1.50	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 3 V		0.05	100	μA
DETECTO	DR					
I <sub>DRM</sub>	Peak Blocking Current, Either Direction	$V_{DRM} = 600 \text{ V}, I_F = 0^{(1)}$		10	100	nA
V <sub>TM</sub>	Peak On-State Voltage, Either Direction	$I_{TM}$ = 100 mA peak, $I_F$ = 0		1.7	2.5	V
dv/dt	Critical Rate of Rise of Off-State Voltage	I <sub>F</sub> = 0 (Figure 13, at 400V)	1000			V/µs

### **Transfer Characteristics**

Symbol	DC Characteristics	Test Conditions	Device	Min.	Тур.	Max.	Unit
	LED Trigger Current,	Main Terminal	MOC3051M			15	mA
IFT	Either Direction	Voltage = $3 V^{(2)}$	MOC3052M			10	IIIA
Ι <sub>Η</sub>	Holding Current, Either Direction		All		220		μA

### **Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Input-Output Isolation Voltage <sup>(3)</sup>	f = 60 Hz, $t = 1 Minute$	4170			$VAC_RMS$
R <sub>ISO</sub>	Isolation Resistance	$V_{I-O} = 500 V_{DC}$		10 <sup>11</sup>		Ω
C <sub>ISO</sub>	Isolation Capacitance	V = 0 V, f = 1 MHz		0.2		pF

#### Notes:

- 1. Test voltage must be applied within dv/dt rating.
- All devices are guaranteed to trigger at an I<sub>F</sub> value less than or equal to max I<sub>FT</sub>. Therefore, the recommended operating I<sub>F</sub> lies between maximum I<sub>F</sub> (15 mA for MOC3051M, 10 mA for MOC3052M) and absolute maximum I<sub>F</sub> (60 mA).
- 3. Isolation voltage, V<sub>ISO</sub>, is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 4, 5 and 6 are common.

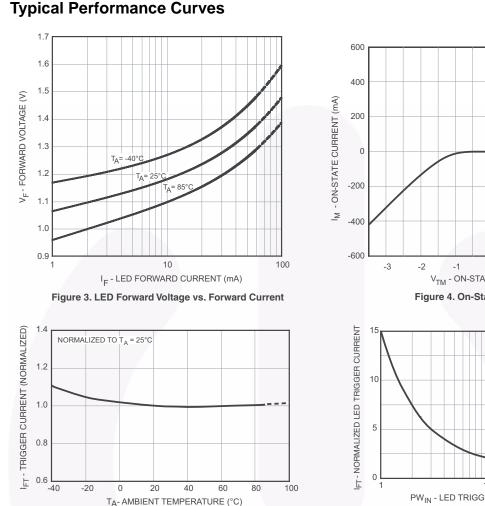


Figure 5. Trigger Current vs. Ambient Temperature

## I<sub>F</sub> vs. Temperature (normalized)

Figure 5 shows the increase of the trigger current when the device is expected to operate at an ambient temperature below 25°C. Multiply the normalized  $I_{FT}$  shown on this graph with the data sheet guaranteed  $I_{FT}$ .

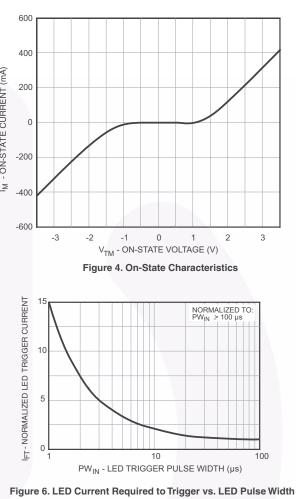
## Example:

 $T_A = 25^{\circ}C, I_{FT} = 10 \text{ mA}$  $I_{FT} \text{ at } -40^{\circ}C = 10 \text{ mA x } 1.1 = 11 \text{ mA}$ 

### **Phase Control Considerations**

### LED Trigger Current versus PW (normalized)

Random Phase Triac drivers are designed to be phase controllable. They may be triggered at any phase angle within the AC sine wave. Phase control may be accomplished by an AC line zero cross detector and a variable pulse delay generator which is synchronized to the zero



cross detector. The same task can be accomplished by a microprocessor which is synchronized to the AC zero crossing. The phase controlled trigger current may be a very short pulse which saves energy delivered to the input LED. LED trigger pulse currents shorter than 100  $\mu$ s must have an increased amplitude as shown on Figure 6. This graph shows the dependency of the trigger current I<sub>FT</sub> versus the pulse width can be seen on the chart delay t(d) versus the LED trigger current.

 $I_{FT}$  in the graph  $I_{FT}$  versus (PW) is normalized in respect to the minimum specified  $I_{FT}$  for static condition, which is specified in the device characteristic. The normalized  $I_{FT}$  has to be multiplied with the devices guaranteed static trigger current.

#### Example:

Guaranteed I<sub>FT</sub> = 10 mA, Trigger pulse width PW = 3  $\mu s$  I<sub>FT</sub> (pulsed) = 10 mA x 5 = 50 mA

# Minimum LED Off Time in Phase Control Applications

In Phase control applications one intends to be able to control each AC sine half wave from 0° to 180°. Turn on at 0° means full power and turn on at 180° means zero power. This is not quite possible in reality because triac driver and triac have a fixed turn on time when activated at zero degrees. At a phase control angle close to 180° the driver's turn on pulse at the trailing edge of the AC sine wave must be limited to end 200 µs before AC zero cross as shown in Figure 7. This assures that the triac driver has time to switch off. Shorter times may cause loss of control at the following half cycle.

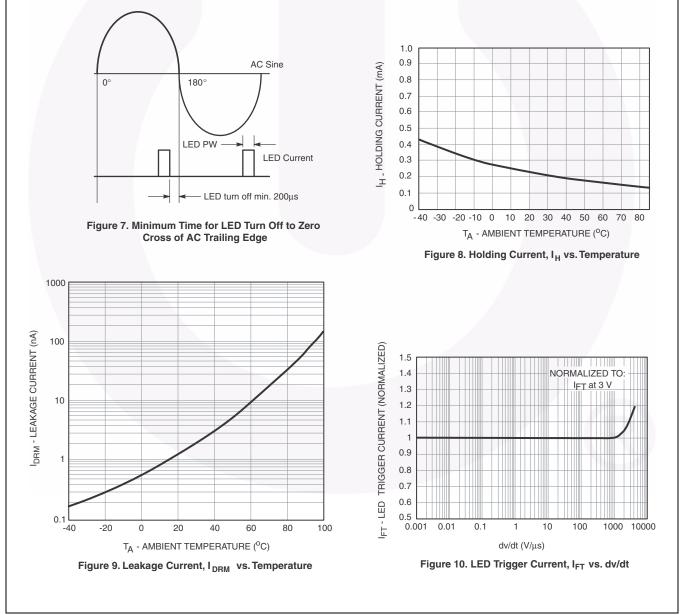
#### IFT versus dv/dt

Triac drivers with good noise immunity (dv/dt static) have internal noise rejection circuits which prevent false

triggering of the device in the event of fast raising line voltage transients. Inductive loads generate a commutating dv/dt that may activate the triac drivers noise suppression circuits. This prevents the device from turning on at its specified trigger current. It will in this case go into the mode of "half waving" of the load. Half waving of the load may destroy the power triac and the load.

Figure 10 shows the dependency of the triac drivers  $I_{FT}$  versus the reapplied voltage rise with a Vp of 400V. This dv/dt condition simulates a worst case commutating dv/dt amplitude.

It can be seen that the  $I_{FT}$  does not change until a commutating dv/dt reaches 1000V/µs. The data sheet specified  $I_{FT}$  is therefore applicable for all practical inductive loads and load factors.



#### t(delay), t(f) versus IFT

The triac driver's turn on switching speed consists of a turn on delay time t(d) and a fall time t(f). Figure 12 shows that the delay time depends on the LED trigger current, while the actual trigger transition time t(f) stays constant with about one micro second.

The delay time is important in very short pulsed operation because it demands a higher trigger current at very short trigger pulses. This dependency is shown in the graph  $I_{FT}$  vs. LED PW.

The turn on transition time t(f) combined with the power triac's turn on time is important to the power dissipation of this device.

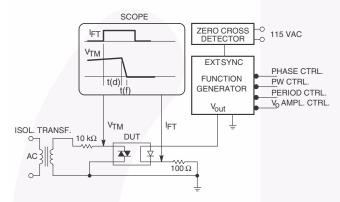


Figure 11. Switching Time Test Circuit

td

tf

IFT - LED TRIGGER CURRENT (mA)

Figure 12. Delay Time, t(d), and Fall Time, t(f),

vs. LED Trigger Current

40

50

60

30

- 1. The mercury wetted relay provides a high speed repeated pulse to the D.U.T.
- 2. 100x scope probes are used, to allow high speeds and voltages.
- 3. The worst-case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable  $R_{TEST}$  allows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering.  $\tau_{RC}$  is measured at this point and recorded.

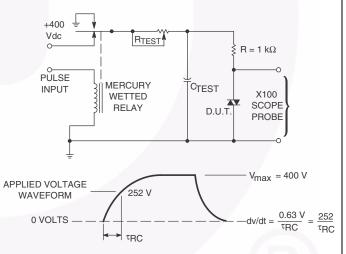


Figure 13. Static dv/dt Test Circuit

10

(delay) AND t(fall) (∞s)

0.1

10

20

## **Applications Guide**

#### **Basic Triac Driver Circuit**

The new random phase triac driver family MOC3052M and MOC3051M are very immune to static dv/dt which allows snubberless operations in all applications where external generated noise in the AC line is below its guaranteed dv/dt withstand capability. For these applications a snubber circuit is not necessary when a noise insensitive power triac is used. Figure 14 shows the circuit diagram. The triac driver is directly connected to the triac main terminal 2 and a series Resistor R which limits the current to the triac driver. Current limiting resistor R must have a minimum value which restricts the current into the driver to maximum 1 A.

#### R = Vp AC / I<sub>TM</sub> max rep. = Vp AC / 1 A

The power dissipation of this current limiting resistor and the triac driver is very small because the power triac carries the load current as soon as the current through driver and current limiting resistor reaches the trigger current of the power triac. The switching transition times for the driver is only one micro second and for power triacs typical four micro seconds.

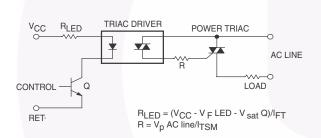


Figure 14. Basic Driver Circuit

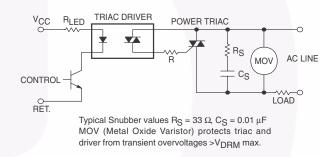


When the transient rate of rise and amplitude are expected to exceed the power triacs and triac drivers maximum ratings a snubber circuit as shown in Figure 15 is recommended. Fast transients are slowed by the R-C snubber and excessive amplitudes are clipped by the Metal Oxide Varistor MOV.

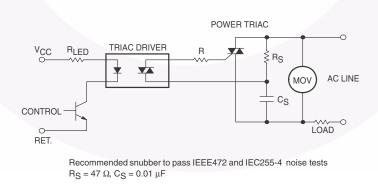
#### Triac Driver Circuit for Extremely Noisy Environments

As specified in the noise standards IEEE472 and IEC255-4.

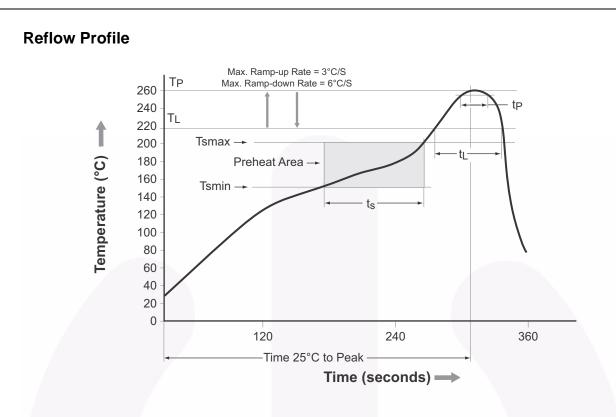
Industrial control applications do specify a maximum transient noise dv/dt and peak voltage which is superimposed onto the AC line voltage. In order to pass this environment noise test a modified snubber network as shown in Figure 16 is recommended.



#### Figure 15. Triac Driver Circuit for Noisy Environments







Profile Freature	Pb-Free Assembly Profile		
Temperature Minimum (Tsmin)	150°C		
Temperature Maximum (Tsmax)	200°C		
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60 seconds to 120 seconds		
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second maximum		
Liquidous Temperature (T <sub>L</sub> )	217°C		
Time $(t_L)$ Maintained Above $(T_L)$	60 seconds to 150 seconds		
Peak Body Package Temperature	260°C +0°C / –5°C		
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds		
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second maximum		
Time 25°C to Peak Temperature	8 minutes maximum		

Figure 17. Reflow Profile

## Ordering Information<sup>(4)</sup>

Part Number	Package	Packing Method
MOC3051M	DIP 6-Pin	Tube (50 Units)
MOC3051SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
MOC3051SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
MOC3051VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3051SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3051SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
MOC3051TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

#### Note:

4. The product orderable part number system listed in this table also applies to the MOC3052M product families.

## **Marking Information**

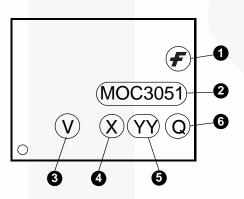
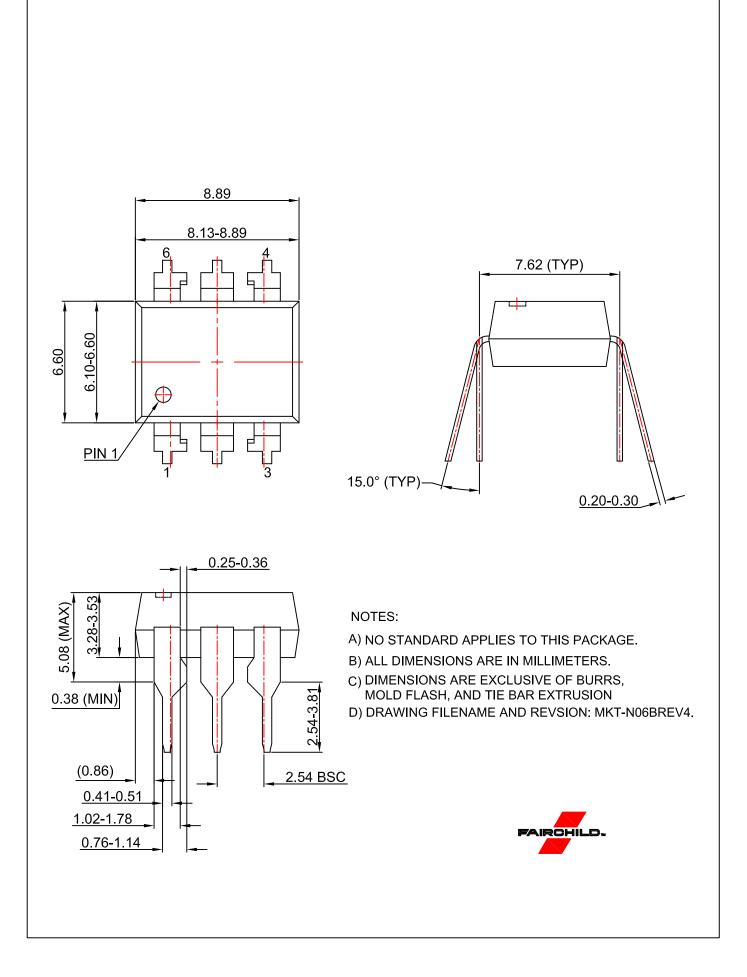
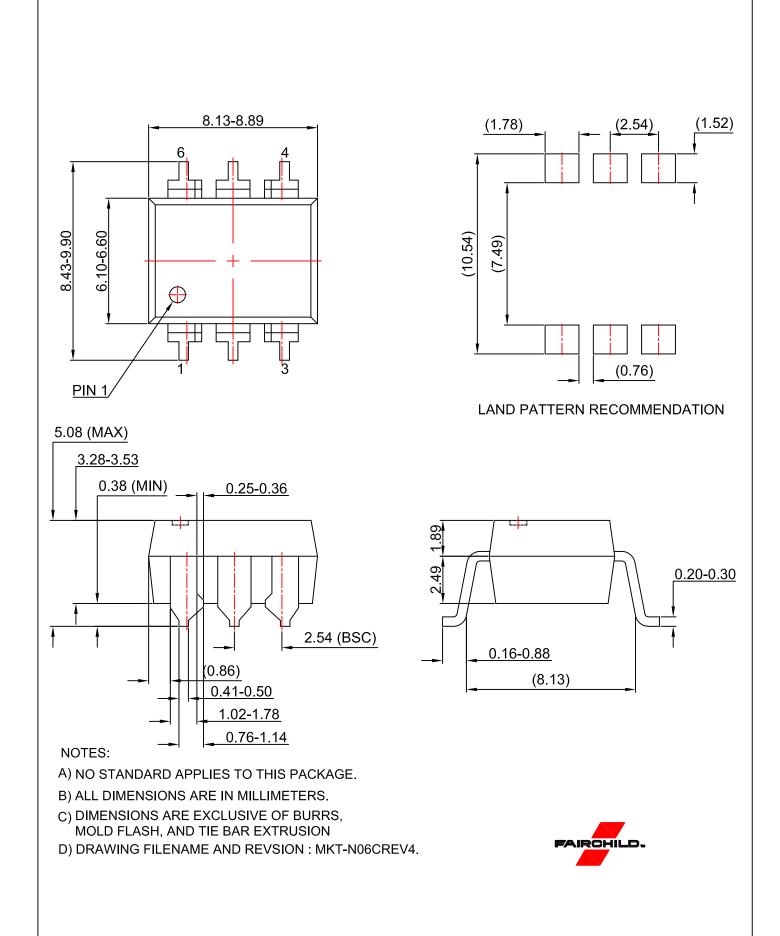
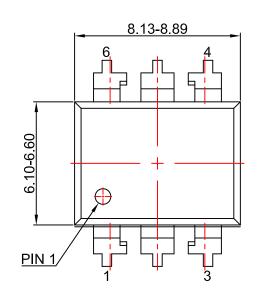


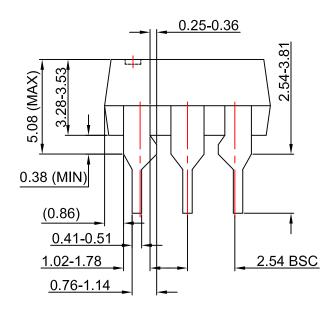
Figure 18. Top Mark

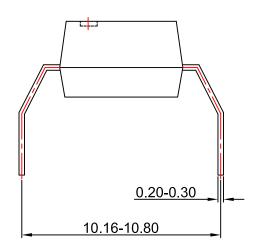
Тор Ма	Top Mark Definitions				
1	Fairchild Logo				
2	Device Number				
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)				
4	One-Digit Year Code, e.g., '5'				
5	Two-Digit Work Week, Ranging from '01' to '53'				
6	Assembly Package Code				











## NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVSION: MKT-N06Drev4





\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT <u>HTTP://WWW.FAIRCHILDSEMI.COM</u>, FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Terms of Use

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### **PRODUCT STATUS DEFINITIONS**

Definition of Terms		
Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 177